Low-Voltage Circuits Using Multiple-Input Floating-Gate MOS Transistors

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- Not robust to drift in Q, or changes in $I_{\rm b}$ or temperature.







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- This form is robust against (matched) drift in Q, changes in $I_{\rm b}$, and temperature.
- One $V_{\rm b}$ generator can be shared by multiple regulated cascodes.







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- This venerable circuit has headroom problems as the supply voltage shrinks.
- Its minimum allowable $V_{\rm cm}$ is about $V_{\rm diode} + V_{\rm sat}$.





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- Unfortunately, as $V_{\rm cm}$ approaches $V_{\rm DD}$, V gets there first...
- Moreover, this solution is not robust to changes in $I_{\rm b}$.





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- In this circuit, called the inverted differential pair, I_1+I_2 is regulated via indirect negative feedback.
- Node V moves in the opposite direction as does $V_{\rm cm}$, whence the name.
- This circuit has a rail-to-rail common-mode input range, a wide output swing, and a constant $G_{\rm m}!$







Experimental Results: I/V Characteristics $I_{\rm b} = 0.316 \,\mathrm{nA}$







Experimental Results: I/V Characteristics $I_{\rm b} = 3.16 \,\mathrm{nA}$







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Experimental Results: I/V Characteristics $I_{\rm b} = 10.0 \,\mu \text{A}$







Experimental Results: I/V Characteristics $I_{\rm b} = 31.6 \,\mu \text{A}$







Experimental Results: $G_{\rm m}$ versus $V_{\rm cm}$







Experimental Results: $I_1 + I_2$ versus V_{out}





